

Silicon NPN Power Transistors

2SC1826

DESCRIPTION

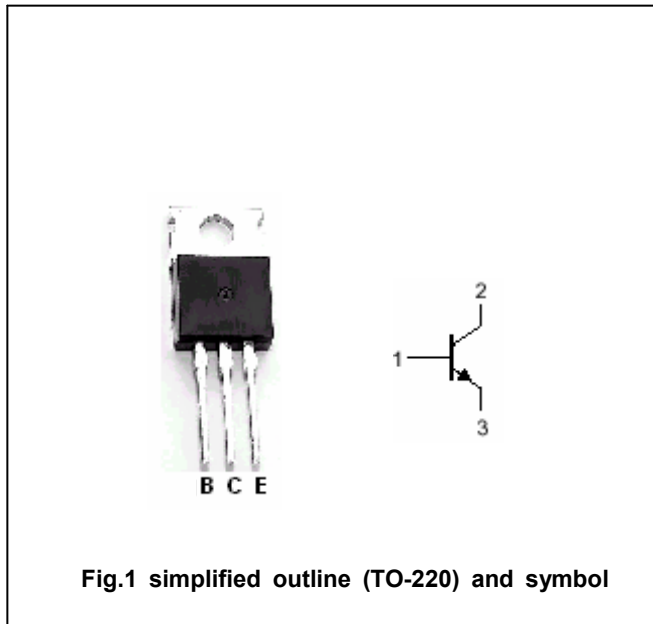
- With TO-220 package
- Collector current : $I_C=4A$
- Collector power dissipation : $P_C=30W@T_C=25^\circ$

APPLICATIONS

- For use in low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings ($T_a=25^\circ$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	80	V
V_{CEO}	Collector-emitter voltage	Open base	60	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current (DC)		4	A
P_C	Collector power dissipation	$T_C=25^\circ$	30	W
T_j	Junction temperature		150	$^\circ$
T_{stg}	Storage temperature		-55~150	$^\circ$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =25mA ; I _B =0	60			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	80			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =3A; I _B =0.3A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =3A ; I _B =0.3A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =80V; I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			100	μA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =4V	40		320	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =12V		10		MHz

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PACKAGE OUTLINE

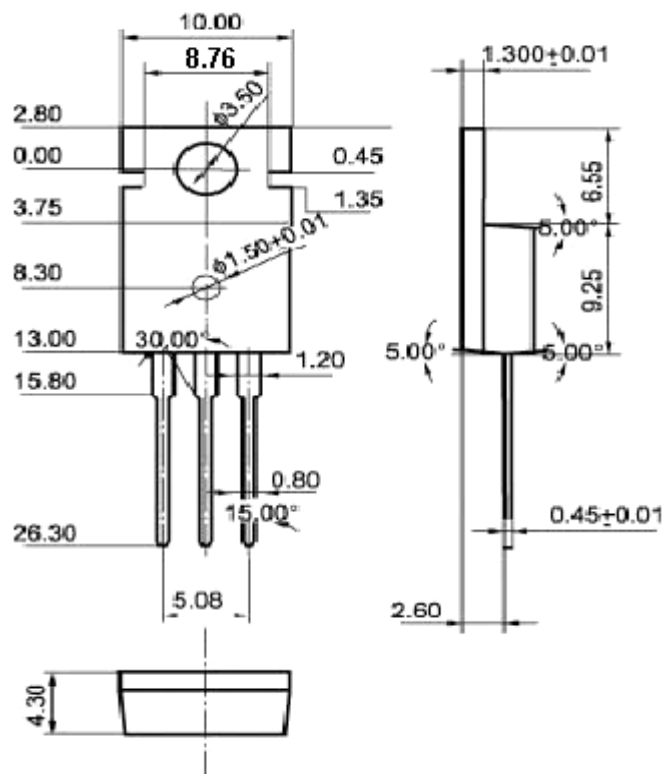


Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)